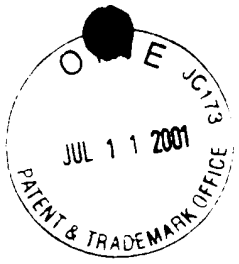
CS-00-122



July 12, 2001

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject: Serial No. 09/838,513 04/20/01

Shaoyin Chen, Ze Xiang Shen,
Alex See, Lap Chan

A NOVEL METHOD TO FORM C54 TiSi2
FOR IC DEVICE FABRICATION

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,937,325 to Ishida, "Formation of Low Resistivity Titanium Silicide Gates in Semiconductor Integrated Circuits", teaches using laser annealing to from C49 TiSi2, then a rapid thermal annealing (RTA) to form C54 TiSi2 on a polysilicon gate.

U.S. Patent 6,054,387 to Fukuda, "Method for Forming a Silicide Region", teaches forming C49 TiSi2 by RTA, then warping the device while performing a second RTA to form C54 TiSi2.

U.S. Patent 6,071,552 to Ku, "Insitu Formation of TiSi2/TiN Bi-Layer Structures Using Self-Aligned Nitridation Treatment on Underlying CVD-TiSi2 Layer", discloses deposition of C49 TiSi2, then an RTA to form C54 TiSi2.

U.S. Patent 5,956,137 to Lim et al., "In-Line Process Monitoring Using Micro-Raman Spectroscopy", discloses a method to use Raman analysis to determine the phase of a silicide.

Sincerely,

George D. Saile

George O. Saile,
Reg. No. 19572